45 V, 100 mA PNP general-purpose transistors
Rev. 1 — 21 February 2012

Product data sheet

### **Product profile**

### 1.1 General description

PNP general-purpose transistors in a leadless ultra small SOT883B Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview** 

Type number	Package		NPN complement	
	NXP	JEITA	JEDEC	
BC857AMB	SOT883B	-	-	BC847AMB
BC857BMB	SOT883B	-	-	BC847BMB
BC857CMB	SOT883B	-	-	BC847CMB

#### 1.2 Features and benefits

- Leadless ultra small SMD plastic
- Low package height of 0.37 mm
- Power dissipation comparable to SOT23
- AEC-Q101 qualified

### 1.3 Applications

- General-purpose switching and amplification
- Mobile applications

#### 1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{CEO}$	collector-emitter voltage	open base	-	-	-45	V
I <sub>C</sub>	collector current		-	-	-100	mA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$				
	BC857AMB		125	-	250	
	BC857BMB		220	-	475	
	BC857CMB		420	-	800	



## 2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline Graphic symbol
1	base	
2	emitter	1 3
3	collector	2 3 1—
		Transparent top view 2
		sym013

## 3. Ordering information

Table 4. Ordering information

Type number	Package		
	Name	Description	Version
BC857xMB series	-	leadless ultra small plastic package; 3 solder lands; body 1.0 $\times$ 0.6 $\times$ 0.37 mm	SOT883B

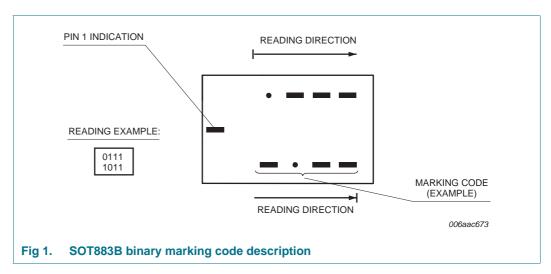
### 4. Marking

Table 5. Marking codes

Type number	Marking code <sup>[1]</sup>
BC857AMB	0100 0100
BC857BMB	0100 0101
BC857CMB	0100 0110

<sup>[1]</sup> For SOT883B binary marking code description, see Figure 1.

### 4.1 Binary marking code description



BC857XMB\_SER

## 5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{CBO}$	collector-base voltage	open emitter		-	-50	V
$V_{CEO}$	collector-emitter voltage	open base		-	<b>-45</b>	V
$V_{EBO}$	emitter-base voltage	open collector		-	<b>-</b> 5	V
I <sub>C</sub>	collector current			-	-100	mA
I <sub>CM</sub>	peak collector current	single pulse; $t_p \le 1 \text{ ms}$		-	-200	mA
I <sub>BM</sub>	peak base current	single pulse; $t_p \le 1 \text{ ms}$		-	-100	mA
P <sub>tot</sub>	total power dissipation	$T_{amb} \le 25  ^{\circ}C$	[1][2]	-	250	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	+150	°C
T <sub>stg</sub>	storage temperature			-65	+150	°C

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

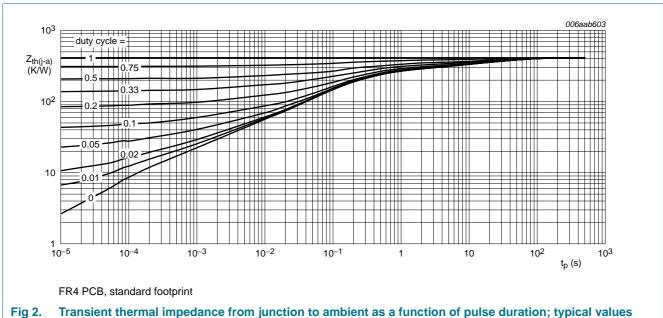
<sup>[2]</sup> Reflow soldering is the only recommended soldering method.

### Thermal characteristics

Table 7. **Thermal characteristics** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1][2] -	-	500	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Reflow soldering is the only recommended soldering method.



Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

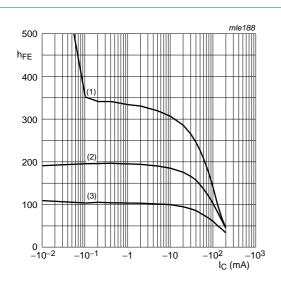
### 7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>CBO</sub>	collector-base	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A}$	-	-	-15	nA
	cut-off current	$V_{CB} = -30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$	-	-	<b>-5</b>	μА
I <sub>EBO</sub>	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-100	nA
h <sub>FE</sub>	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -2 \text{ mA}$				
	BC857AMB BC857BMB		125	-	250	
			220	-	475	
	BC857CMB		420	-	800	
V <sub>CEsat</sub>	collector-emitter	$I_C = -10 \text{ mA}; I_B = -0.5 \text{ mA}$	-	-	-200	mV
	saturation voltage	$I_C = -100 \text{ mA}; I_B = -5 \text{ mA}$	[1] _	-	-400	mV
$V_{BE}$	base-emitter voltage	$I_C = -2 \text{ mA}; V_{CE} = -5 \text{ V}$	-600	-	-750	mV
		$I_C = -10 \text{ mA}; V_{CE} = -5 \text{ V}$	-	-	-820	mV
f <sub>T</sub>	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA};$ f = 100 MHz	100	-	-	MHz
C <sub>c</sub>	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ $f = 1 \text{ MHz}$	-	-	2.5	pF
NF	noise figure	$I_{C} = -200 \ \mu A; \ V_{CE} = -5 \ V; \ R_{S} = 2 \ k\Omega; \ f = 1 \ kHz; \ B = 200 \ Hz$	-	-	10	dB

<sup>[1]</sup> Pulse test:  $t_p \le 300~\mu s;~\delta \le 0.02.$ 



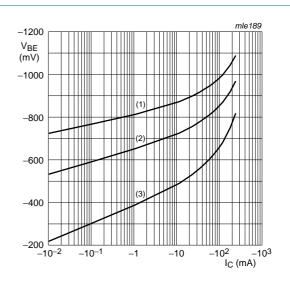
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 3. BC857AMB: DC current gain as a function of collector current; typical values



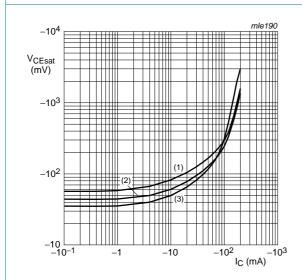
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 4. BC857AMB: Base-emitter voltage as a function of collector current; typical values



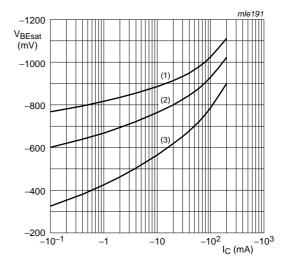


(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 5. BC857AMB: Collector-emitter saturation voltage as a function of collector current; typical values



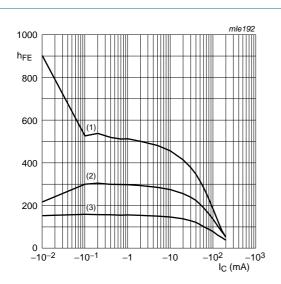
$$I_{\rm C}/I_{\rm B} = 20$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig 6. BC857AMB: Base-emitter saturation voltage as a function of collector current; typical values



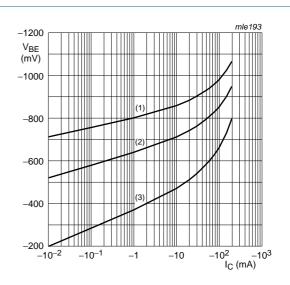
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 7. BC857BMB: DC current gain as a function of collector current; typical values



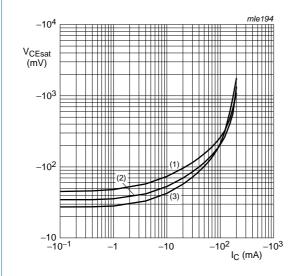
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 8. BC857BMB: Base-emitter voltage as a function of collector current; typical values



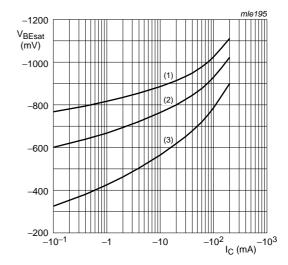
 $I_{\rm C}/I_{\rm B} = 20$ 

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 9. BC857BMB: Collector-emitter saturation voltage as a function of collector current; typical values



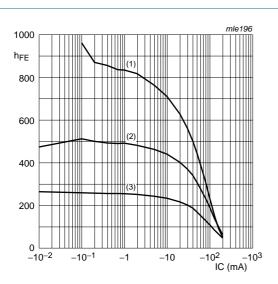
 $I_{\rm C}/I_{\rm B} = 20$ 

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

Fig 10. BC857BMB: Base-emitter saturation voltage as a function of collector current; typical values



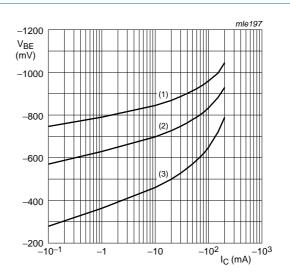
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 11. BC857CMB: DC current gain as a function of collector current; typical values



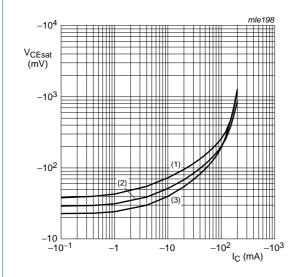
$$V_{CE} = -5 \text{ V}$$

(1) 
$$T_{amb} = -55 \, ^{\circ}C$$

(2) 
$$T_{amb} = 25 \, ^{\circ}C$$

(3) 
$$T_{amb} = 150 \, ^{\circ}C$$

Fig 12. BC857CMB: Base-emitter voltage as a function of collector current; typical values



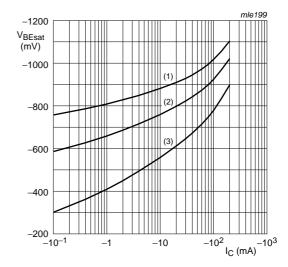
 $I_{\rm C}/I_{\rm B} = 20$ 

(1) 
$$T_{amb} = 150 \, ^{\circ}C$$

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = -55 \, ^{\circ}C$ 

Fig 13. BC857CMB: Collector-emitter saturation voltage as a function of collector current; typical values



 $I_{\rm C}/I_{\rm B} = 20$ 

(1)  $T_{amb} = -55 \, ^{\circ}C$ 

(2)  $T_{amb} = 25 \, ^{\circ}C$ 

(3)  $T_{amb} = 150 \, ^{\circ}C$ 

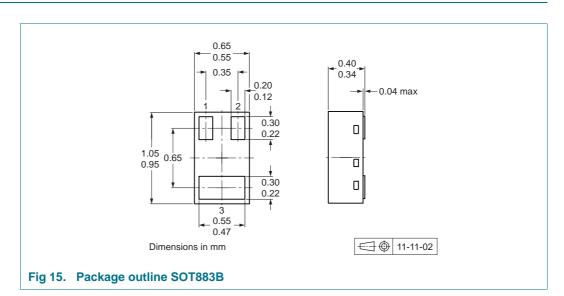
Fig 14. BC857CMB: Base-emitter saturation voltage as a function of collector current; typical values

### 8. Test information

### 8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

### 9. Package outline



## 10. Packing information

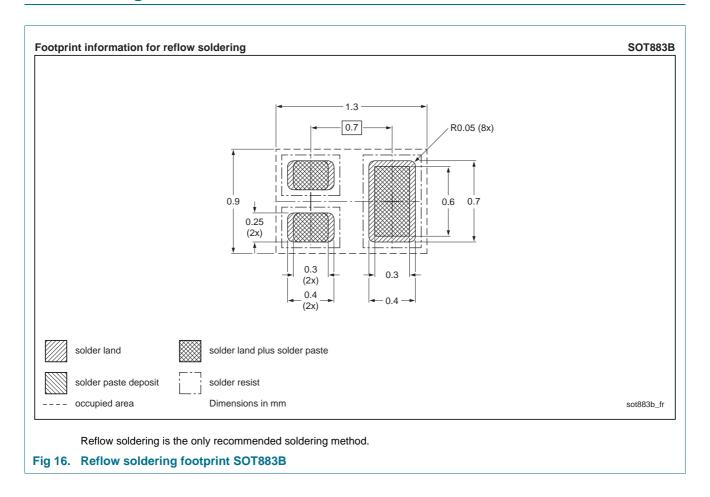
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Description	Packing quantity
			10000
BC857xMB series	SOT883B	2 mm pitch, 8 mm tape and reel	-315

<sup>[1]</sup> For further information and the availability of packing methods, see Section 14.

### 11. Soldering



45 V, 100 mA PNP general-purpose transistors

## 12. Revision history

#### Table 10. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BC857XMB_SER v.1	20120221	Product data sheet	-	-

### 13. Legal information

#### 13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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#### 45 V, 100 mA PNP general-purpose transistors

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### 45 V, 100 mA PNP general-purpose transistors

### 15. Contents

1	Product profile	. 1
1.1	General description	. 1
1.2	Features and benefits	. 1
1.3	Applications	
1.4	Quick reference data	. 1
2	Pinning information	. 2
3	Ordering information	. 2
4	Marking	. 2
4.1	Binary marking code description	. 2
5	Limiting values	. 3
6	Thermal characteristics	. 4
7	Characteristics	. 5
8	Test information	. 9
8.1	Quality information	. 9
9	Package outline	. 9
10	Packing information	. 9
11	Soldering	10
12	Revision history	11
13	Legal information	12
13.1	Data sheet status	12
13.2	Definitions	12
13.3	Disclaimers	12
13.4	Trademarks	13
14	Contact information	13
15	Contents	14

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